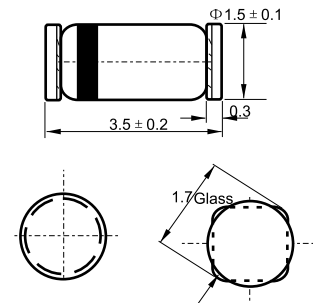




MINI MELF



Dimension in millimeters

Features

- ✧ Fast Switching Speed
- ✧ Surface Mount Package Ideally Suited for Automatic Insertion
- ✧ General Purpose Rectification
- ✧ Silicon Epitaxial Planar Construction

Mechanical Data

- ✧ Case: MiniMELF
- ✧ Polarity: Cathode Band
- ✧ Marking: Cathode Band Only
- ✧ Weight: 0.12 grams (approx.)

Maximum Ratings and Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified.

Maximum Ratings

Characteristic	Symbol	LL4148	LL4448	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	110		V
Peak Repetitive Reverse Voltage	V_{RRM}	100		V
Working Peak Reverse Voltage	V_{RWM}			
DC Blocking Voltage	V_R			
RMS Reverse Voltage	$V_{R(RMS)}$	53		V
Forward Continuous Current (Note 1)	I_{FM}	300	500	mA
Average Rectified Output Current (Note 1)	I_O	150		mA
Non-Repetitive Peak Forward Surge Current @ t = 1.0s @ t = 1.0μs	I_{FSM}	1.0 2.0		A
Power Dissipation (Note 1) Derate Above 25°C	P_d	500 1.68		mW mW/°C
Thermal Resistance, Junction to Ambient Air (Note 1)	$R_{\theta JA}$	300		K/W
Operating and Storage Temperature Range	T_j, T_{STG}	-65 to +175		°C

Electrical Characteristics

Characteristic	Symbol	Min	Max	Unit	Test Condition
Maximum Forward Voltage LL4148 LL4448 LL4448	V_{FM}	— 0.62 —	1.0 0.72 1.0	V	$I_F = 10mA$ $I_F = 5.0mA$ $I_F = 100mA$
Maximum Peak Reverse Current	I_{RM}	—	5.0 50 30 25	μA μA μA nA	$V_R = 75V$ $V_R = 70V, T_j = 150°C$ $V_R = 20V, T_j = 150°C$ $V_R = 20V$
Capacitance	C_j	—	4.0	pF	$V_R = 0, f = 1.0MHz$
Reverse Recovery Time	t_{rr}	—	4.0	ns	$I_F = 10mA$ to $I_R = 1.0mA$ $V_R = 6.0V, R_L = 100Ω$

Notes: 1. Valid provided that device terminals are kept at ambient temperature.

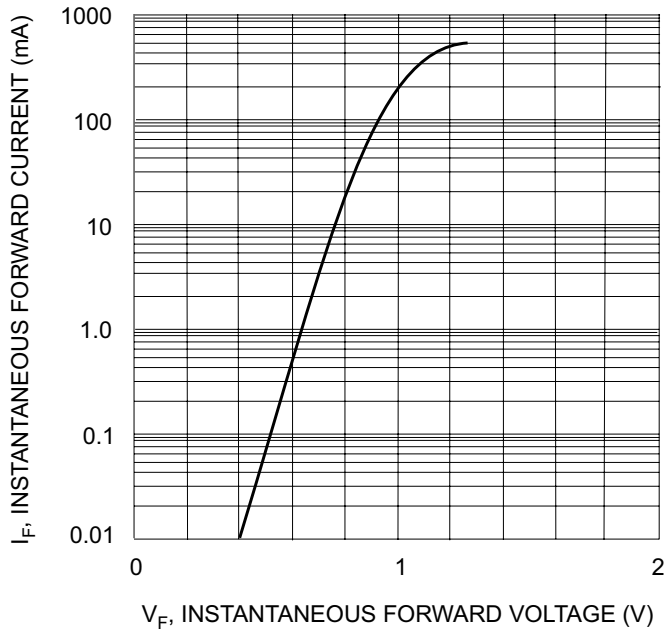


Fig. 1 Forward Characteristics

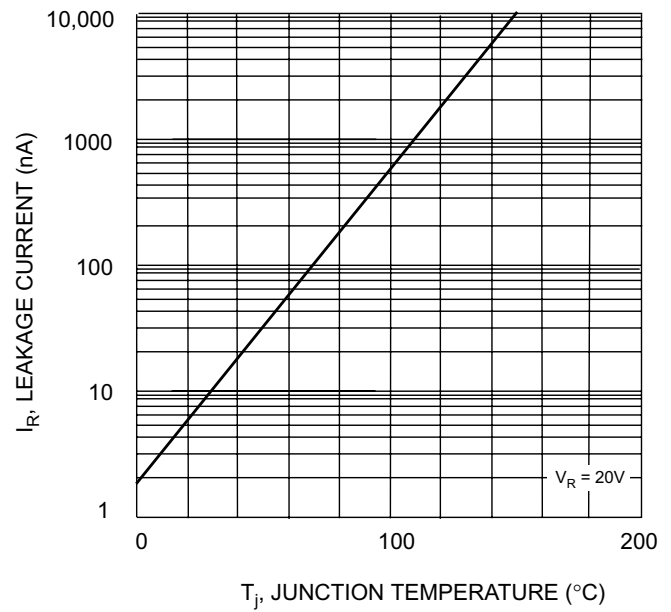


Fig. 2, Leakage Current vs Junction Temperature